

International
IOR Rectifier

IR155DM16CCB SERIES

STANDARD RECOVERY DIODES

- Junction Size: Square 155 mils
- Wafer Size: 4"
- V_{RRM} Class: 1600 V
- Passivation Process: Glassivated MOAT
- Reference IR Packaged Part: 15ETS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1100 mV	$T_J = \text{Amb.}, I_F = 15 \text{ A}$
V_{RRM} Reverse Breakdown Voltage Range	1600 V (*)	$T_J = \text{Amb.}, I_{RRM} = 50 \mu\text{A}$ (**)

(*) Wafer and die Probe test clamped at 1200V to limit arcing. **1600V BV testable only in encapsulated packages**

(**) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	155 x 155 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	330 μm , $\pm 10 \mu\text{m}$
Maximum Width of Sawing Line	110 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

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Preliminary Data Sheet I0146J 02/02

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Ordering Information Table

Device Code						
IR	155	D	M	16	C	CB
①	②	③	④	⑤	⑥	⑦

- 1** - International Rectifier Device
- 2** - Chip Dimension in Mils
- 3** - Type of Device: D = Wire Bondable Standard Recovery Diode
- 4** - Passivation Process: M = Glassivated MOAT
- 5** - Voltage code: Code x 100 = V_{RRM}
- 6** - Metallization: C = Aluminium (Anode) - Silver (Cathode)
- 7** - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

Outline Table

